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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Fumio HORIGUCHI

SERIAL NUMBER: 10/073,339

GROUP: 2824

FILED: February 13, 2002

EXAMINER: TRAN, ANDREW Q

FOR: MULTI-VALUE MAGNETIC RANDOM ACCESS MEMORY WITH STACKED TUNNEL MAGNETORESISTANCE (TMR) ELEMENTS

REQUEST TO CORRECT TITLE OF INVENTION

MAIL STOP ISSUE FEE COMMISSIONER FOR PATENTS P.O. BOX 1450 ALEXANDRIA, VA 22313-1450

SIR:

In the matter of the above-identified application for patent, we hereby request correction of your records to reflect the correct title of the invention. The title of the invention should read as follows: MULTI-VALUE MAGNETIC RANDOM ACCESS MEMORY WITH STACKED TUNNEL MAGNETORESISTANCE (TMR)

ELEMENTS.

Respectfully Submitted,

OBLON, SPIVAK, McCLELLAND, MAIER & NEUSTADT, P.C.

Marvin J. Spivak

Registration No. 24,913

Surinder Sachar Registration No. 34,423

Customer Number

22850

Tel. (703) 413-3000 Fax. (703) 413-2220 (OSMMN 05/04)